



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-23 Plastic-Encapsulate Transistors

2SB624 TRANSISTOR (PNP)

FEATURES

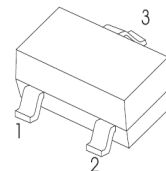
- High DC current gain. h_{FE} :200 TYP.($V_{CE}=-1V, I_C=-100mA$)
- Complimentary to 2SD596.

MAXIMUM RATINGS ($T_a=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-30	V
V_{CEO}	Collector-Emitter Voltage	-25	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-700	mA
P_D	Total Device Dissipation	200	mW
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature	-55-150	$^{\circ}C$

SOT-23

1.BASE
2.EMITTER
3.COLLECTOR



ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu A, I_E=0$	-30			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1mA, I_B=0$	-25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu A, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-30V, I_E=0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5V, I_C=0$			-0.1	μA
DC current gain	$h_{FE(1)}^*$	$V_{CE}=-1V, I_C=-100mA$	110		400	
	$h_{FE(2)}^*$	$V_{CE}=-1V, I_C=-700mA$	50			
Collector-emitter saturation voltage	$V_{CE(sat)}^*$	$I_C=-700mA, I_B=-70mA$			-0.6	V
Base-emitter voltage	V_{BE}^*	$V_{CE}=-6V, I_C=-10mA$	-0.6		-0.7	V
Transition frequency	f_T	$V_{CE}=-6V, I_C=-10mA$		160		MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=-6V, I_E=0, f=1MHz$		17		pF

* Pulse test : Pulse width $\leq 350\mu s$, Duty Cycle $\leq 2\%$.

CLASSIFICATION OF $h_{FE(1)}$

Marking	BV1	BV2	BV3	BV4	BV5
Range	110-180	135-220	170-270	200-320	250-400